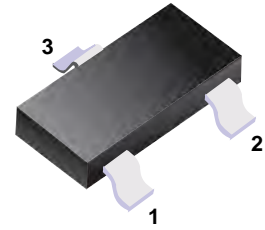


■ **Features**

- Excellent ON resistance
- Supper high density cell design
- ESD protected(HBM) up to 2KV
- $V_{DS}= 20V, I_D= 0.8A$
 $R_{DS(on)} < 310m\Omega @ V_{GS}= 4.5V$

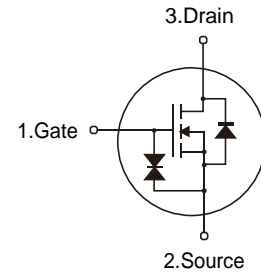
■ **Applications**

- DC-DC converter circuit
- Load switch
- Small Signal Switch



1. Gate
2. Source
3. Drain

■ **Simplified outline(SOT-23)**



■ **Absolute Maximum Ratings** ($T_a = 25^\circ C$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Drain Current-Continuous	I_D	0.8	A
Drain Current-Pulsed ^{Note1}	I_{DM}	3.2	A
Maximum Power Dissipation	P_D	0.35	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ C$
Thermal Resistance,Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	357	$^\circ C/W$



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■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	--	--	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$	--	--	± 10	μA
Gate Threshold Voltage ^{Note3}	$V_{GS(h)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.8	1	V
Drain-Source On-Resistance ^{Note3}	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.55A$	--	220	310	m Ω
		$V_{GS}=2.5V, I_D=0.5A$	--	260	360	m Ω
Forward Transconductance ^{Note3}	g_{FS}	$V_{DS}=5V, I_D=0.5A$	--	2	--	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, f=1KHz$	--	50	--	pF
Output Capacitance	C_{oss}		--	13	--	pF
Reverse Transfer Capacitance	C_{rss}		--	8	--	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=0.55A$ $V_{GS}=4.5V, R_G=6\Omega$	--	22	--	nS
Turn-on Rise Time	t_r		--	80	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	700	--	nS
Turn-off Fall Time	t_f		--	380	--	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=0.55A,$ $V_{GS}=4.5V$	--	1.15	--	nC
Gate-Source Charge	Q_{gs}		--	0.15	--	nC
Gate-Drain Charge	Q_{gd}		--	0.23	--	nC
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	V_{SD}	$V_{GS}=0V, I_S=0.5A$	--	0.7	1.3	V
Diode Forward Current ^{Note2}	I_S		--	--	0.8	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

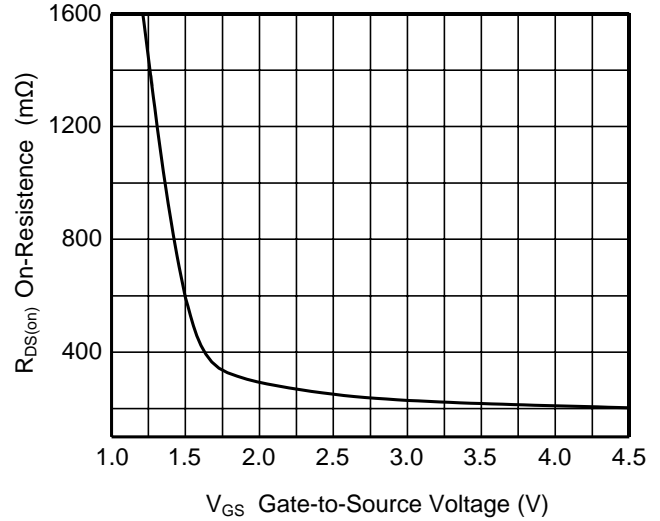
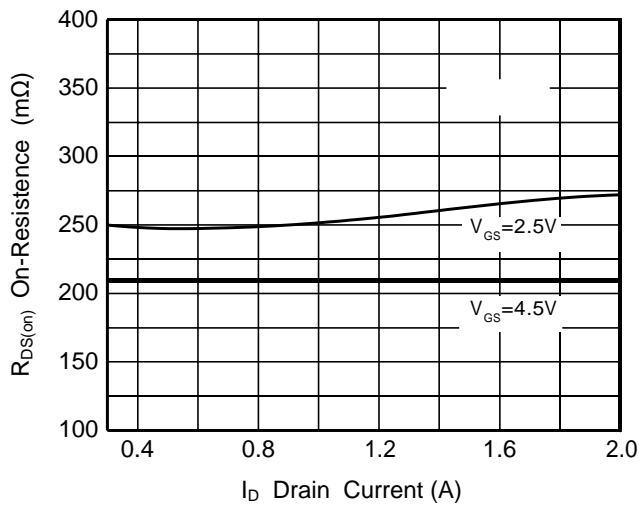
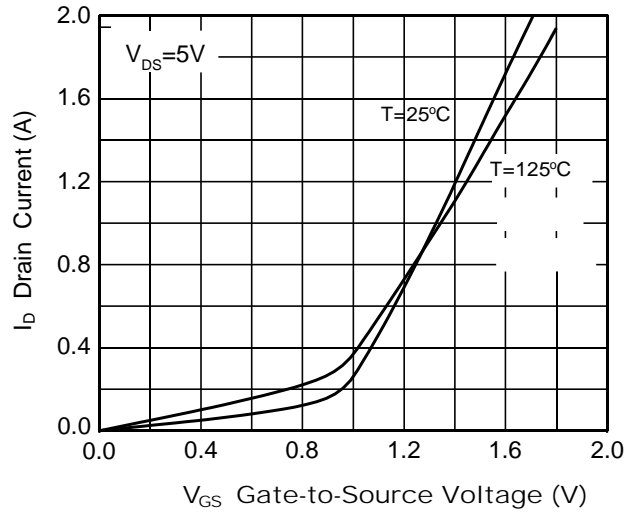
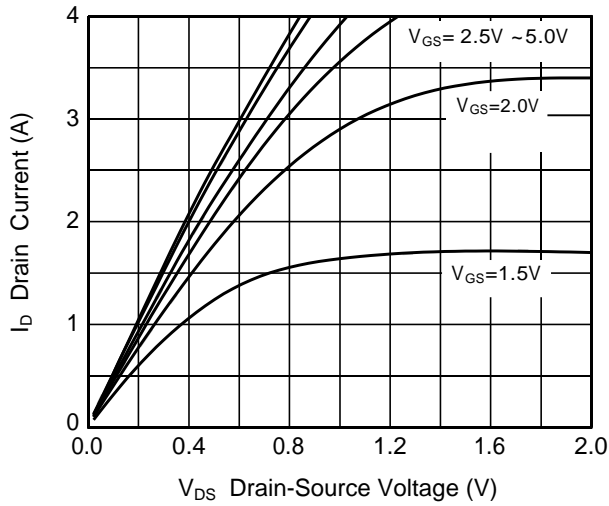
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

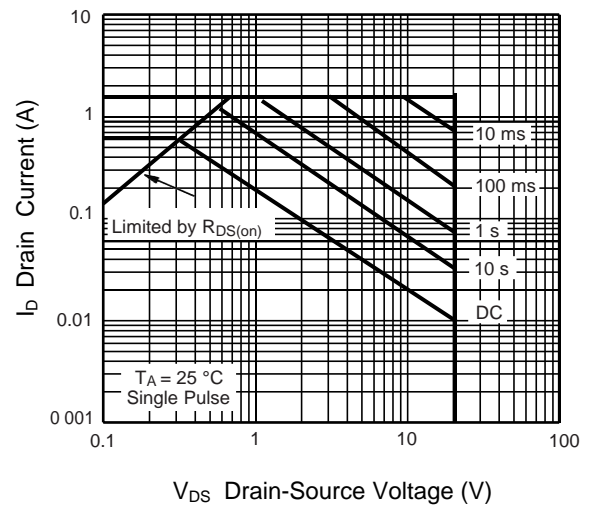
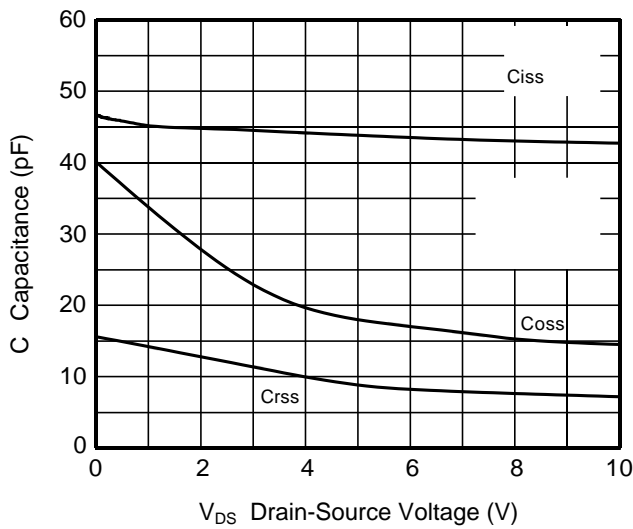
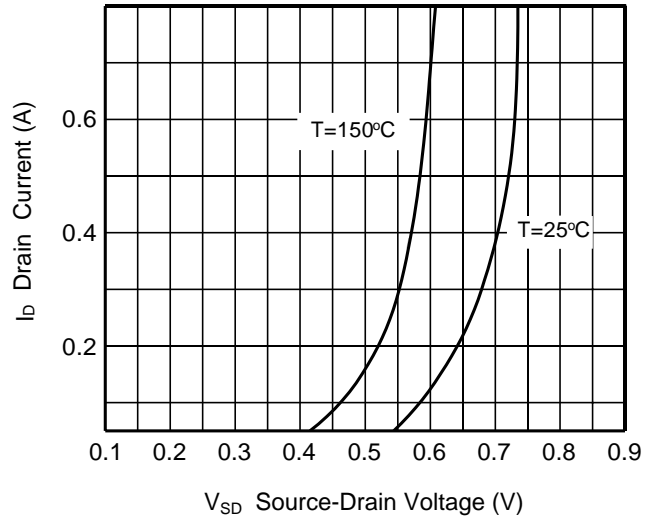
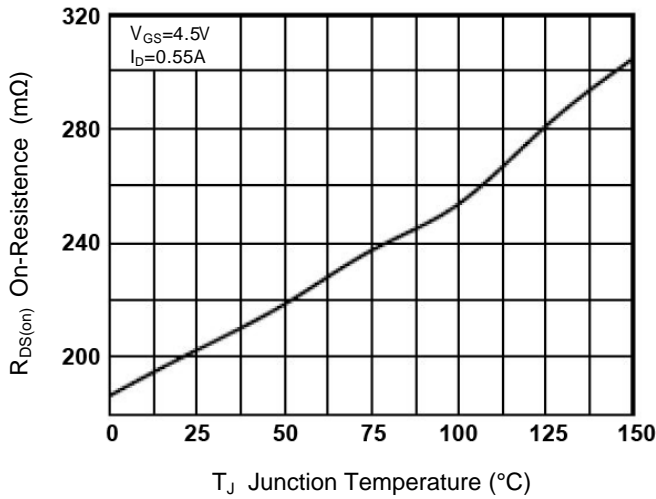


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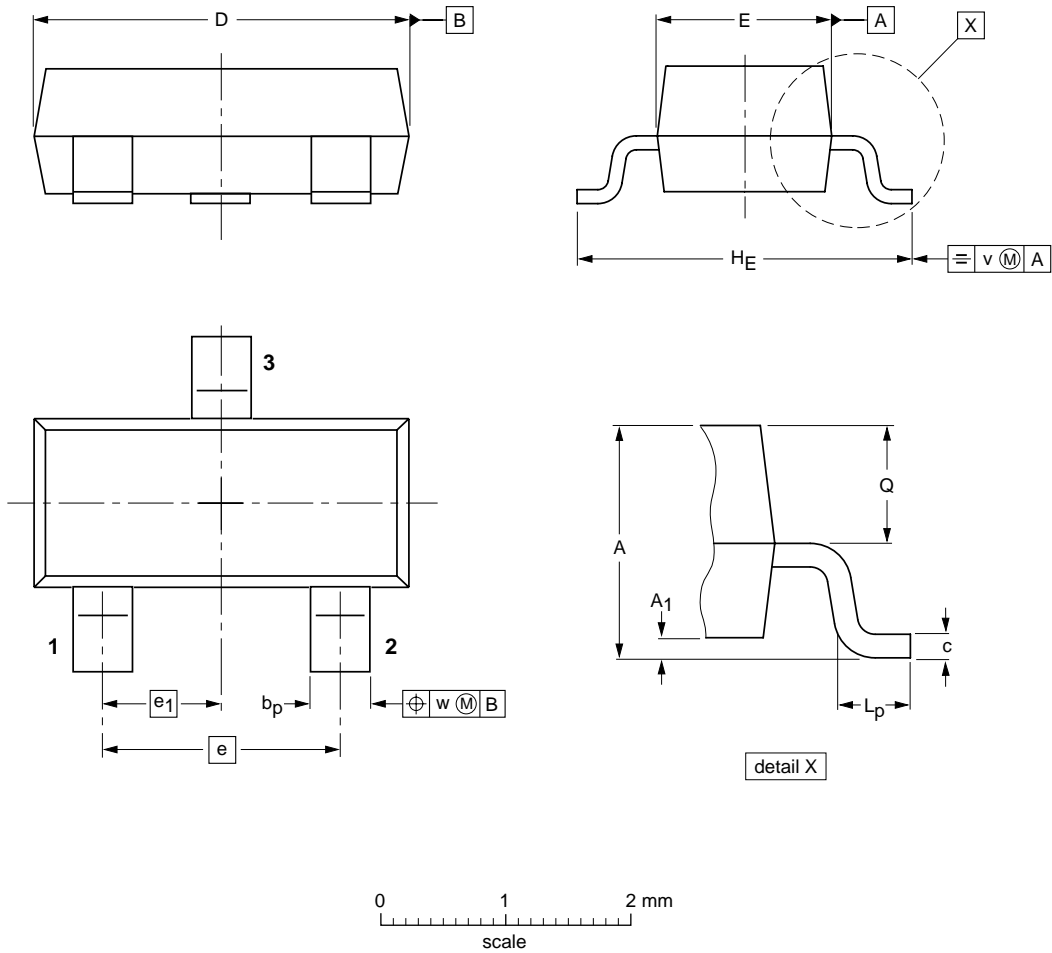
Typical Performance Characteristics



Typical Performance Characteristics(Con.)



■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1